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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	lc	-600	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D-	310	mW	
Power Dissipation	(Note 7)	P _D	350		
Thermal Resistance, Junction to Ambient	(Note 6)	Ь	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	R _{θJA} 357		
Thermal Resistance, Junction to Leads	(Note 8)	$R_{\theta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

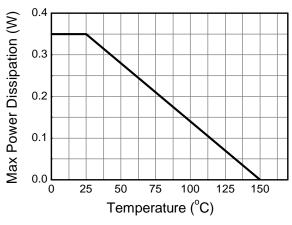
 7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.

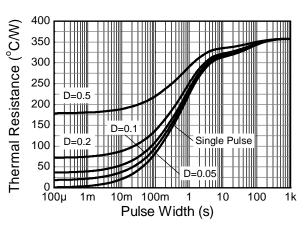
 8. Thermal resistance from junction to solder-point (at the end of the leads).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



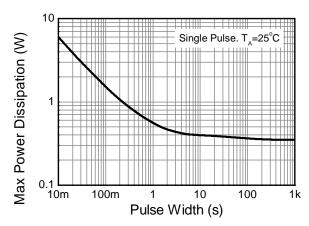
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)					
Collector-Base Breakdown Voltage	BV_{CBO}	-160		V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-150	_	V	$I_C = -1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	-50 -50	nA	$V_{CB} = -120V, I_E = 0$
Further Outs' Outside				μA	$V_{CB} = -120V, I_E = 0, T_A = +100^{\circ}C$
Emitter Cutoff Current	I _{EBO}		-50	nA	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 10)					
	h _{FE}	50	_		$I_C = -1 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain		60	240	_	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
		50	—		$I_C = -50 \text{mA}, V_{CE} = -5 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	E(SAT) —	-0.2 -0.5	V	$I_C = -10mA, I_B = -1mA$
Collector-Emilier Saturation voltage					$I_C = -50 \text{mA}, I_B = -5 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1	V	$I_C = -10mA$, $I_B = -1mA$
· ·					$I_C = -50 \text{mA}, I_B = -5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_obo	_	6	pF	$V_{CB} = -10V$, $f = 1MHz$, $I_E = 0$
Small Signal Current Gain	h _{fe}	40	260	_	$V_{CE} = -10V, I_{C} = -1mA,$ f = 1kHz
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA,$ f = 100MHz
Noise Figure	NF	_	8.0	dB	V_{CE} = -5V, I_C = -200 μ A, R_S = 10 Ω , f = 1kHz

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

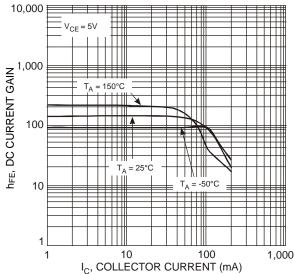
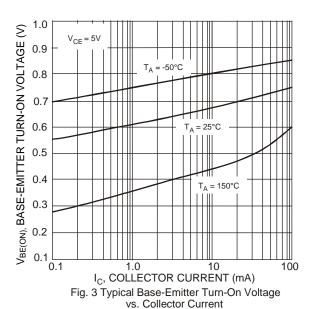


Fig. 1 Typical DC Current Gain vs. Collector Current



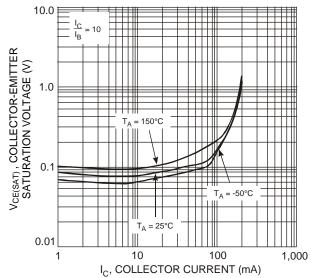


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

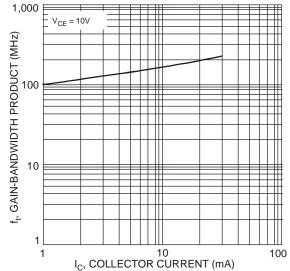


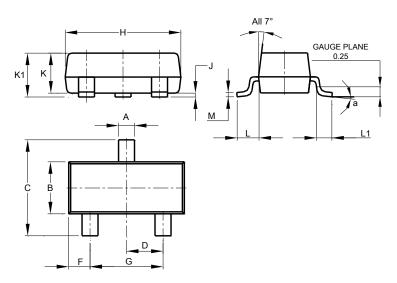
Fig.4 Typical Gain-Bandwidth Product vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

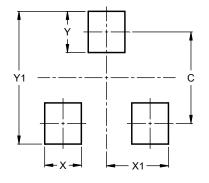


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
U	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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